



### SIHB33N60E-GE3 Information



For Reference Only

**Part Number** SIHB33N60E-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 33A TO-263

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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### **SIHB33N60E-GE3 Specifications**

Manufacturer Part NumberSIHB33N60E-GE3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C33A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μA	
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB  Series  - Series  - N-Channel  MOSFET (Metal Oxide)  100V	
Transistors - FETs, MOSFETs - Single  Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB  Series - FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  10V	
Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB  Series -  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 600V  Current - Continuous Drain (Id) @ 25°C 33A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V	
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Vgs(th) (Max) @ Id 4V @ 250μA	
Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds 3508pF @ 100V	
Vgs (Max) ±30V	
FET Feature -	
Power Dissipation (Max) 278W (Tc)	
Rds On (Max) @ Id, Vgs 99 mOhm @ 16.5A, 10V	
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	
Mounting Type Surface Mount	
Supplier Device Package D2PAK	
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
	Report errors?

#### SIHB33N60E-GE3 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### SIHB33N60E-GE3 Payment Methods



















## SIHB33N60E-GE3 Shipping Methods













If you have any question about SIHB33N60E-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com